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April 2014

FQA62N25C

N-Channel QFET® MOSFET

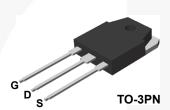
250 V, 62 A, 35 mΩ

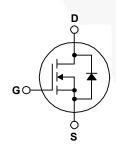
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- + 62 A, 250 V, $R_{DS(on)}$ = 35 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 31 A
- Low Gate Charge (Typ. 100 nC)
- Low Crss (Typ. 63.5 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQA62N25C	Unit
V_{DSS}	Drain-Source Voltage	250	V
I _D	Drain Current - Continuous (T _C = 25°C)	62	Α
	- Continuous (T _C = 100°C)	39	Α
I _{DM}	Drain Current - Pulsed (Note 1)	248	Α
V_{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	2300	mJ
I _{AR}	Avalanche Current (Note 1)	62	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)	29.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation (T _C = 25°C)	298	W
	- Derate above 25°C	2.38	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FQA62N25C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA62N25C	FQA62N25C	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions		Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.28		V/°C
I _{DSS}	Zero Cata Valta de Dueiro Cumant	V _{DS} = 250 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 200 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 31 A		0.029	0.035	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 31 A		55		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		4830	6280	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		945	1230	pF
C _{rss}	Reverse Transfer Capacitance			63.5	83	pF
	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 125 V, I _D = 62 A,		75	160	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		395	800	ns
$t_{d(off)}$	Turn-Off Delay Time			245	500	ns
t _f	Turn-Off Fall Time	(Note 4)		335	680	ns
Qg	Total Gate Charge	V _{DS} = 200 V, I _D = 62 A,		100	130	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		25.5		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		39		nC

Drain-Source Diode Characteristics and Maximum Ratings

Is	Maximum Continuous Drain-Source Diode Forward Current				62	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				248	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 62 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 62 A,		340		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		4.77	/	μС

- **Notes:** 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 0.96 mH, I_{AS} = 62 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. $I_{SD} \le$ 62 A, di/dt \le 300 A/ μ s, $V_{DD} \le$ BV $_{DSS}$, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Performance Characteristics

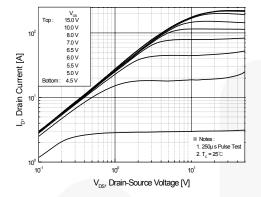


Figure 1. On-Region Characteristics

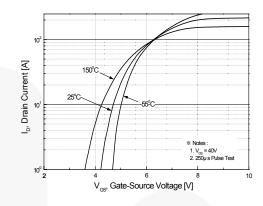


Figure 2. Transfer Characteristics

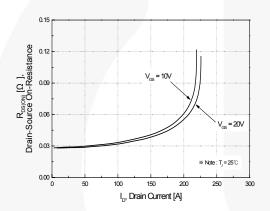


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

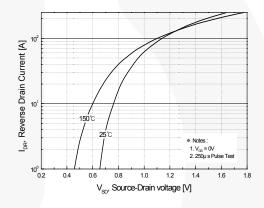


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

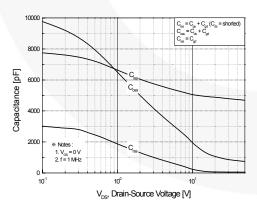


Figure 5. Capacitance Characteristics

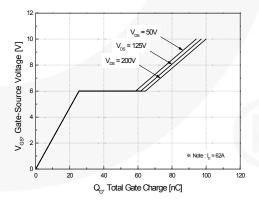


Figure 6. Gate Charge Characteristics

Typical Performance Characteristics (Continued)

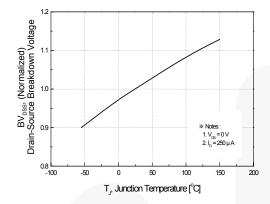


Figure 7. Breakdown Voltage Variation vs Temperature

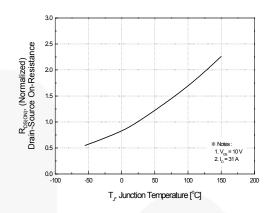


Figure 8. On-Resistance Variation vs Temperature

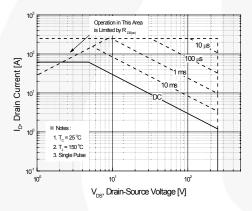


Figure 9. Maximum Safe Operating Area

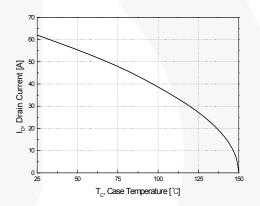


Figure 10. Maximum Drain Current vs Case Temperature

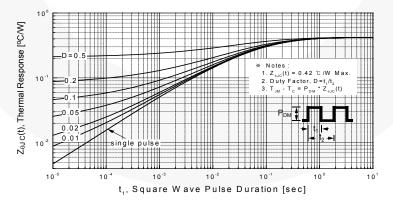


Figure 11. Transient Thermal Response Curve

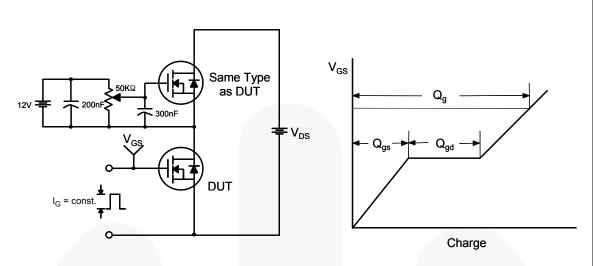


Figure 12. Gate Charge Test Circuit & Waveform

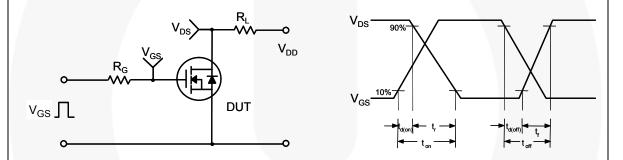


Figure 13. Resistive Switching Test Circuit & Waveforms

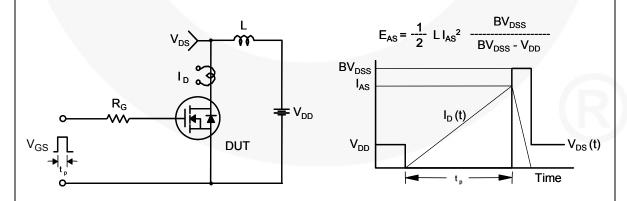
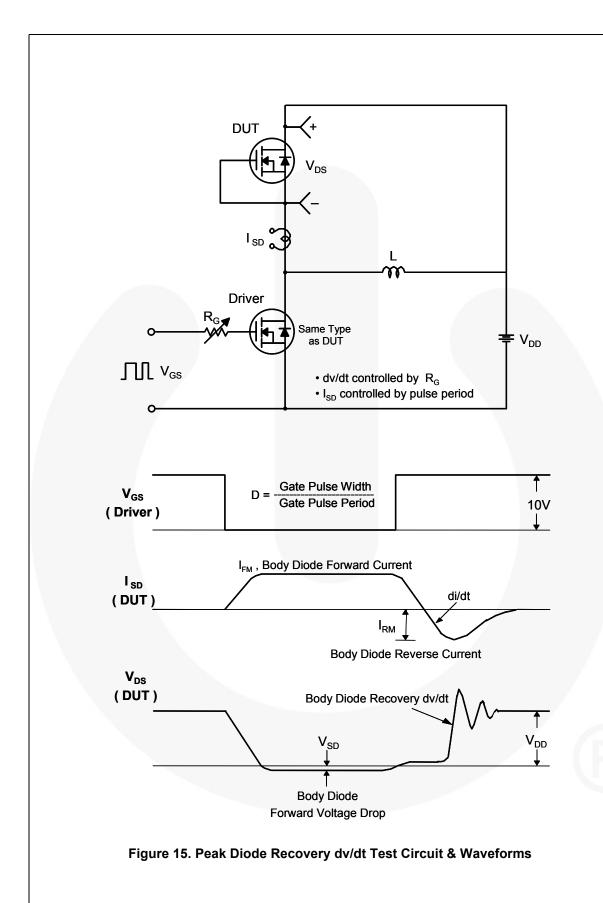
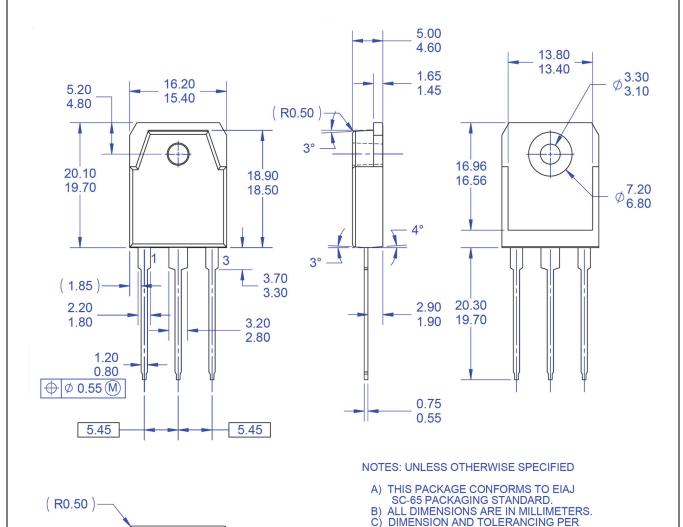


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions



ASME14.5-2009.

D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
E) DRAWING FILE NAME: TO3PN03AREV1.

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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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